SFT1342

Power MOSFET

-60V, 62mΩ, -12A, Single P-Channel

ON Semiconductor®

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Features

- Low On-Resistance
- Low Gate Charge
- Pb-free and RoHS Compliance
- High Speed Switching
- ESD Diode-Protected Gate

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter		Symbol	Value	Unit
Drain to Source Voltage		V _{DSS}	-60	V
Gate to Source Voltage		VGSS	±20	V
Drain Current (DC)		ID	-12	Α
Drain Current PW≤10μs, duty cycle≤1%		I _{DP}	-48	А
Power Dissipation		PD	1.0	W
	Tc=25°C		15	W
Junction Temperature		Tj	150	°C
Storage Temperature		Tstg	-55 to +150	°C

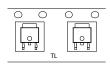
Thermal Resistance Ratings

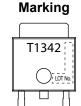
Parameter	Symbol	Value	Unit
Junction to Case Steady State	$R_{\theta JC}$	8.33	0000
Junction to Ambient *1	$R_{\theta JA}$	125	°C/W

Note: *1 Insertion mounted

P-Channel

Packing Type:TL









Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

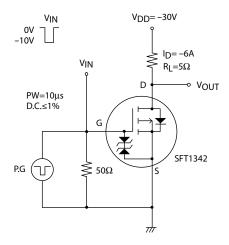
SFT1342

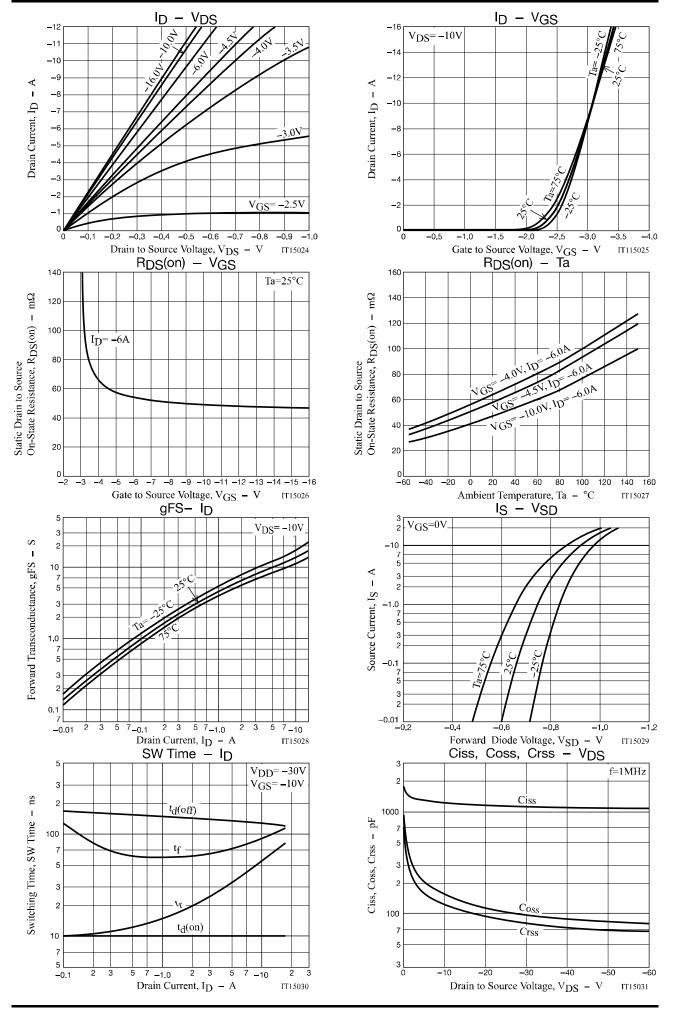
Electrical Characteristics at Ta = 25°C

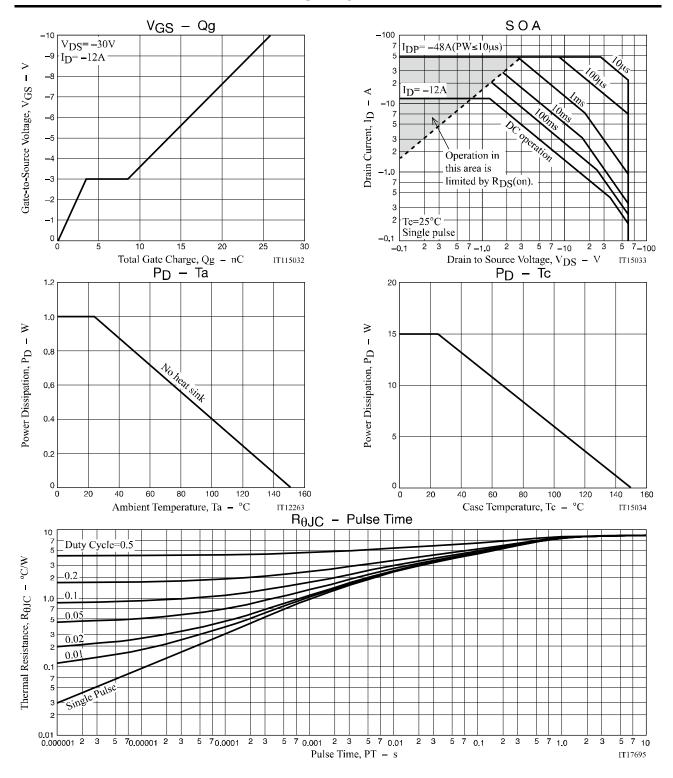
B	0	0 1111		Value		
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D = -1mA, V _G S=0V	-60			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} = -60V, V _{GS} =0V			-1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	V _{GS} (th)	$V_{DS} = -10V, I_{D} = -1mA$	-1.2		-2.6	>
Forward Transconductance	9FS	V _{DS} = -10V, I _D = -6A		11		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D = -6A, V _{GS} = -10V		47	62	mΩ
	R _{DS} (on)2	I _D = -6A, V _G S= -4.5V		62	87	mΩ
	R _{DS} (on)3	I _D = -6A, V _G S= -4V		68	96	mΩ
Input Capacitance	Ciss			1150		pF
Output Capacitance	Coss	V _{DS} = -20V, f=1MHz		115		pF
Reverse Transfer Capacitance	Crss			95		pF
Turn-ON Delay Time	t _d (on)			10		ns
Rise Time	t _r]		37		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		135		ns
Fall Time	tf			75		ns
Total Gate Charge	Qg			26		nC
Gate to Source Charge	Qgs	V _{DS} = -30V, V _{GS} = -10V, I _D = -12A		3.5		nC
Gate to Drain "Miller" Charge	Qgd	7		5		nC
Forward Diode Voltage	V _{SD}	I _S = -12A, V _{GS} =0V		-0.95	-1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit







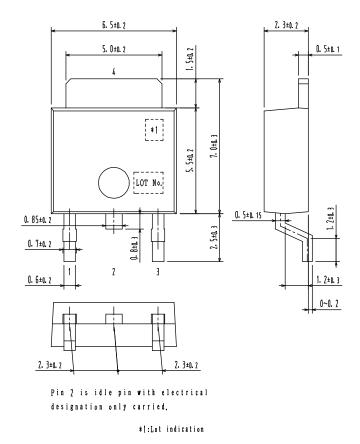
Package Dimensions SFT1342-TL-E/ SFT1342-TL-W

DPAK/TP-FA

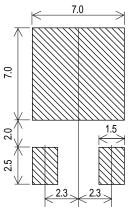
unit: mm



- 1:Gate
- 2:Drain
- 3:Source
- 4:Drain



Recommended **Soldering Footprint**



Package Dimensions

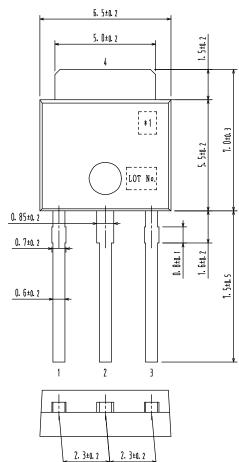
SFT1342-E/ SFT1342-W

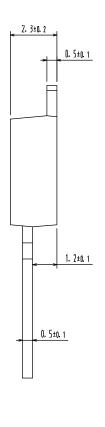
IPAK/TP

Unit: mm



- 1:Gate
- 2:Drain
- 3:Source
- 4:Drain





*1:Lot indication

Ordering & Package Information

Device	Package	Shipping	Note	
SFT1342-E	IPAK(TP)		Pb-Free	
SFT1342-W	SC-64,TO-251	500pcs. / bag	Pb-Free and Halogen Free	
SFT1342-TL-E	DPAK(TP-FA)	700 /	Pb-Free	
SFT1342-TL-W	SC-63,TO-252	700pcs. / reel	Pb-Free and Halogen Free	

Note on usage: Since the SFT1342 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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